

To all our customers

Regarding the change of names mentioned in the document, such as Hitachi Electric and Hitachi XX, to Renesas Technology Corp.

The semiconductor operations of Mitsubishi Electric and Hitachi were transferred to Renesas Technology Corporation on April 1st 2003. These operations include microcomputer, logic, analog and discrete devices, and memory chips other than DRAMs (flash memory, SRAMs etc.) Accordingly, although Hitachi, Hitachi, Ltd., Hitachi Semiconductors, and other Hitachi brand names are mentioned in the document, these names have in fact all been changed to Renesas Technology Corp. Thank you for your understanding. Except for our corporate trademark, logo and corporate statement, no changes whatsoever have been made to the contents of the document, and these changes do not constitute any alteration to the contents of the document itself.

Renesas Technology Home Page: <http://www.renesas.com>

Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

Notes regarding these materials

1. These materials are intended as a reference to assist our customers in the selection of the Renesas Technology Corporation product best suited to the customer's application; they do not convey any license under any intellectual property rights, or any other rights, belonging to Renesas Technology Corporation or a third party.
2. Renesas Technology Corporation assumes no responsibility for any damage, or infringement of any third-party's rights, originating in the use of any product data, diagrams, charts, programs, algorithms, or circuit application examples contained in these materials.

3. All information contained in these materials, including product data, diagrams, charts, programs and algorithms represents information on products at the time of publication of these materials, and are subject to change by Renesas Technology Corporation without notice due to product improvements or other reasons. It is therefore recommended that customers contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor for the latest product information before purchasing a product listed herein.

The information described here may contain technical inaccuracies or typographical errors.

Renesas Technology Corporation assumes no responsibility for any damage, liability, or other loss rising from these inaccuracies or errors.

Please also pay attention to information published by Renesas Technology Corporation by various means, including the Renesas Technology Corporation Semiconductor home page (<http://www.renesas.com>).

4. When using any or all of the information contained in these materials, including product data, diagrams, charts, programs, and algorithms, please be sure to evaluate all information as a total system before making a final decision on the applicability of the information and products. Renesas Technology Corporation assumes no responsibility for any damage, liability or other loss resulting from the information contained herein.
5. Renesas Technology Corporation semiconductors are not designed or manufactured for use in a device or system that is used under circumstances in which human life is potentially at stake. Please contact Renesas Technology Corporation or an authorized Renesas Technology Corporation product distributor when considering the use of a product contained herein for any specific purposes, such as apparatus or systems for transportation, vehicular, medical, aerospace, nuclear, or undersea repeater use.
6. The prior written approval of Renesas Technology Corporation is necessary to reprint or reproduce in whole or in part these materials.
7. If these products or technologies are subject to the Japanese export control restrictions, they must be exported under a license from the Japanese government and cannot be imported into a country other than the approved destination.
Any diversion or reexport contrary to the export control laws and regulations of Japan and/or the country of destination is prohibited.
8. Please contact Renesas Technology Corporation for further details on these materials or the products contained therein.

HD74LS123 ● Dual Retriggerable Monostable Multivibrators (with Clear)

This d-c triggered multivibrator features output pulse width control by three method. The basic pulse time is programmed by selection of external resistance and capacitance values. Once triggered, the basic pulse width may be extended by re-triggering the gated low-level-active (A) or high-level-active (B) inputs, or be reduced by use of the overriding clear. Fig. 1 illustrates pulse control by retriggering and early clear. This device is provided enough Schmitt hysteresis to ensure jitter-free triggering from the B input with transition rates as slow as 0.1 mV/ns.

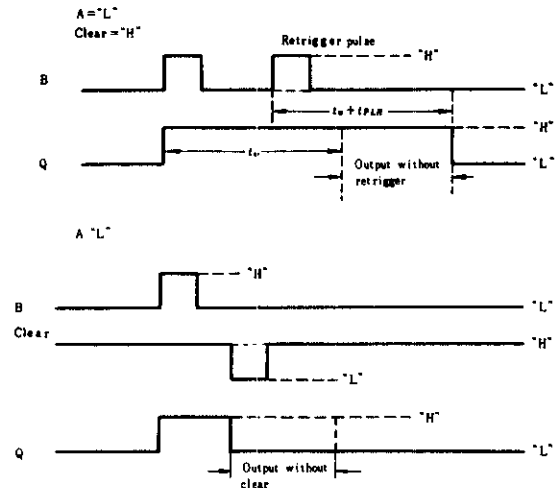
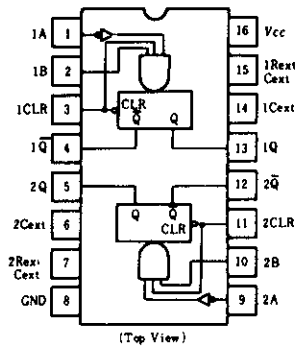


Fig.1 Typical Input/Output Pulses

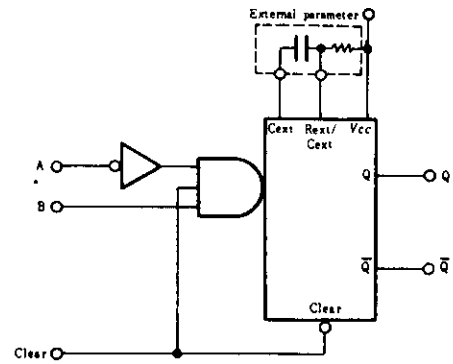
RECOMMENDED OPERATING CONDITIONS

Item	Symbol	min	typ	max	Unit
Input pulse width	A, B "H"	40	—	—	ns
	CLR "L"	40	—	—	ns
	CLR "L"	40	—	—	ns
External timing resistance	R_{ext}	5	—	260	k Ω
External capacitance	C_{ext}	Non restriction			
Wiring capacitance at Rext/Cext terminal		—	—	50	pF

PIN ARRANGEMENT



BLOCK DIAGRAM (1/2)



FUNCTION TABLE

Inputs			Outputs	
CLEAR	A	B	Q	$\bar{Q}$
L	X	X	L	H
X	H	X	L	H
X	X	L	L	H
H	L	↑		
H	↓	H		
↑	L	H		

Notes) H; high level, L; low level, X; irrelevant
↓; transition from high to low level
↑; transition from low to high level
; one high-level pulse
; one low-level pulse

ELECTRICAL CHARACTERISTICS ($T_a = -20 \sim +75^\circ\text{C}$)

Item	Symbol	Test Conditions	min	typ*	max	Unit
Input voltage	V_{IH}		2.0	—	—	V
	V_{IL}		—	—	0.8	V
Output voltage	V_{OH}	$V_{CC}=4.75\text{V}$, $V_{IH}=2\text{V}$, $V_{IL}=0.8\text{V}$, $I_{OH}=-400\mu\text{A}$	2.7	—	—	V
	V_{OL}	$V_{CC}=4.75\text{V}$, $V_{IH}=2\text{V}$, $V_{IL}=0.8\text{V}$	—	—	0.4	V
			—	—	0.5	
Input current	I_{IH}	$V_{CC}=5.25\text{V}$, $V_I=2.7\text{V}$	—	—	20	μA
	I_{IL}	$V_{CC}=5.25\text{V}$, $V_I=0.4\text{V}$	—	—	-0.4	mA
	I_I	$V_{CC}=5.25\text{V}$, $V_I=7\text{V}$	—	—	0.1	mA
Short-circuit output current	I_{OS}	$V_{CC}=5.25\text{V}$	-20	—	-100	mA
Supply current**	I_{CC}	$V_{CC}=5.25\text{V}$	—	12	20	mA
Input clamp voltage	V_{IK}	$V_{CC}=4.75\text{V}$, $I_{IN}=-18\text{mA}$	—	—	-1.5	V

* $V_{CC}=5\text{V}$, $T_a=25^\circ\text{C}$

** With all outputs open and 4.5V applied to all data and clear inputs, I_{CC} is measured after a momentary ground, then 4.5V, is applied clock.

Note) To measure V_{OH} at Q, V_{OL} at $\bar{Q}$, or I_{OS} at Q, ground R_{ext}/C_{ext} , apply 2V to B and clear, and pulse A from 2V to 0V.

SWITCHING CHARACTERISTICS ($V_{CC}=5\text{V}$, $T_a=25^\circ\text{C}$)

Item	Symbol	Inputs	Outputs	Test Conditions	min	typ	max	Unit
Propagation delay time	t_{PLH}	A	Q	$C_{ext}=0\text{pF}$ $R_{ext}=5\text{k}\Omega$ $C_L=15\text{pF}$ $R_L=2\text{k}\Omega$	—	23	33	ns
	t_{PHL}		$\bar{Q}$		—	32	45	
	t_{PLH}	B	Q		—	23	44	
	t_{PHL}		$\bar{Q}$		—	34	56	
	t_{PHL}	CLR	Q		—	20	27	
	t_{PLH}		$\bar{Q}$		—	28	45	
Output pulse width	$t_{out(min)}$	A, B	Q	$C_{ext}=1,000\text{pF}$, $R_{ext}=10\text{k}\Omega$ $C_L=15\text{pF}$, $R_L=2\text{k}\Omega$	—	116	200	μs
	$t_{out(max)}$				4	4.5	5	

TYPICAL APPLICATION DATA FOR HD74LS123

For pulse widths when $C_{ext} < 1000\text{pF}$, See Fig. 3.

The output pulse is primarily a function of the external capacitor and resistor. For $C_{ext} > 1000\text{pF}$, the output pulse width (t_w) is defined as: $t_w(out) = K \cdot R_{ext} \cdot C_{ext}$; See Fig. 4

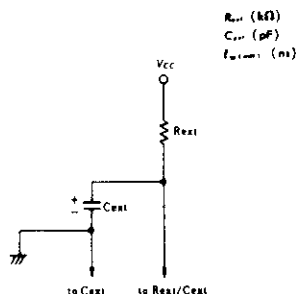


Fig.2 Timing Component Connections

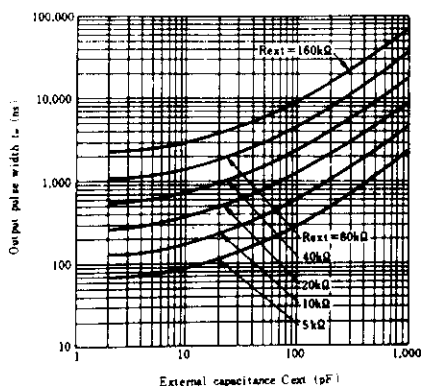


Fig.3 Typical Output Pulse Width ($C_{ext} \leq 1000\text{pF}$)

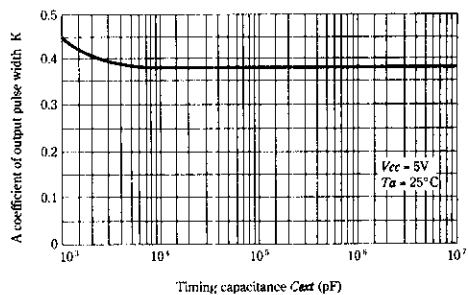
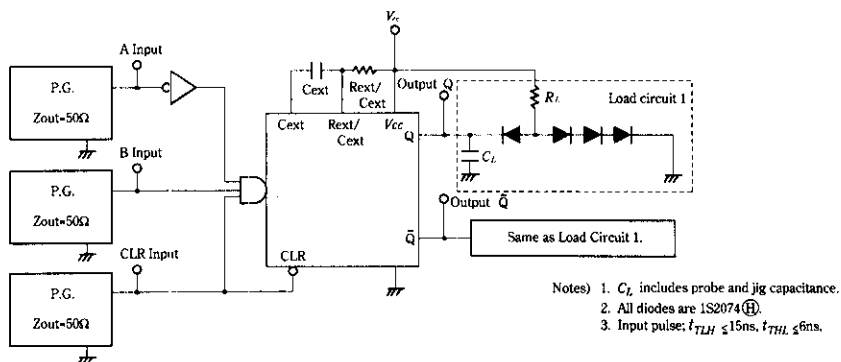


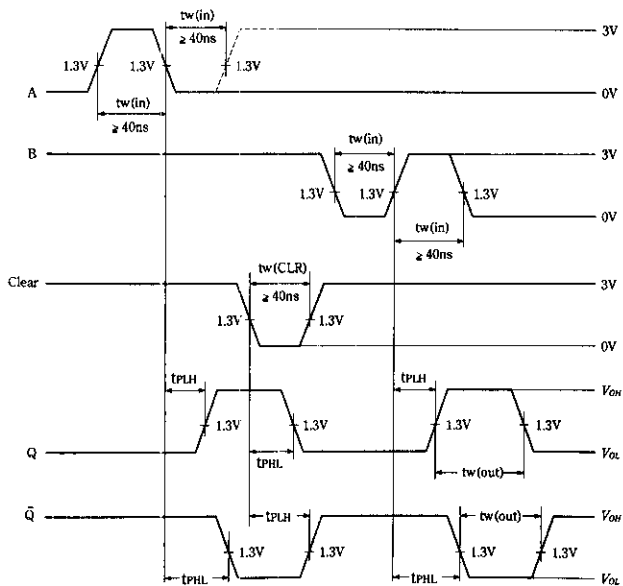
Fig.4 C_{ext} vs K ($C_{ext} > 1000pF$)

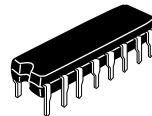
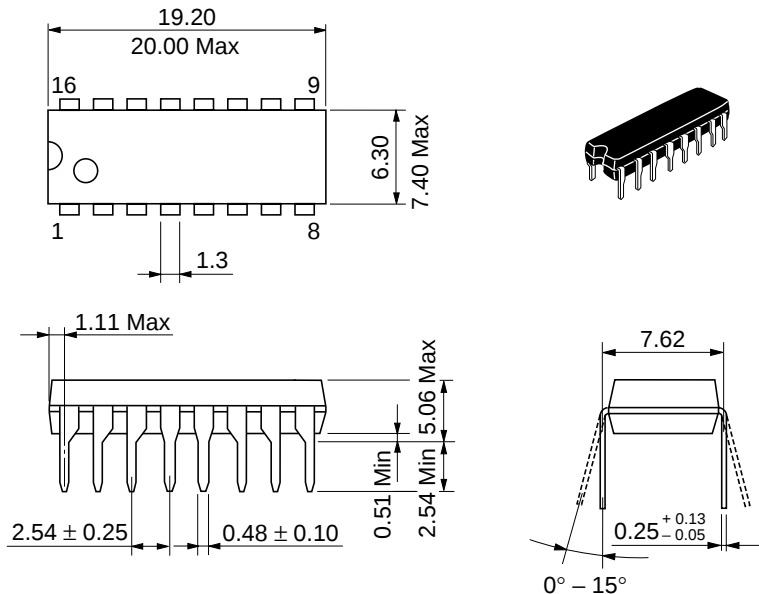
■ TESTING METHOD

1) Test Circuit

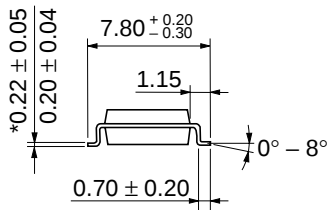
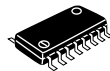
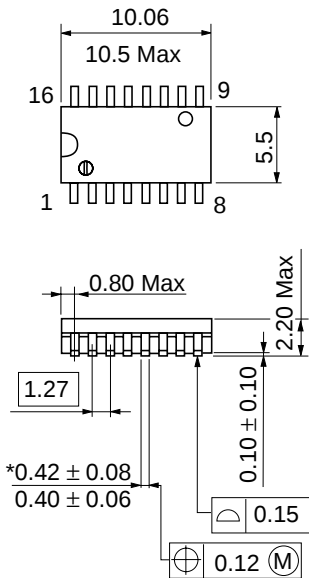


Waveform



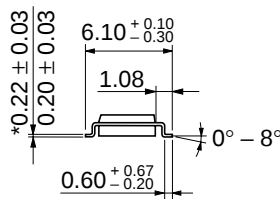
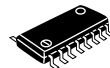
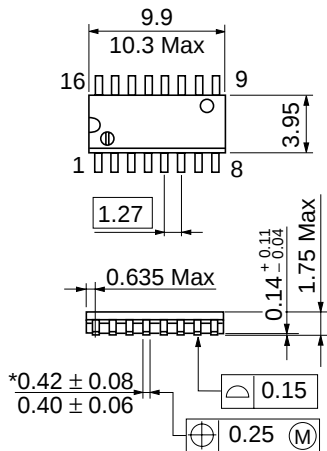


Hitachi Code	DP-16
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	1.07 g



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DA
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.24 g



*Dimension including the plating thickness
Base material dimension

Hitachi Code	FP-16DN
JEDEC	Conforms
EIAJ	Conforms
Weight (reference value)	0.15 g

Cautions

1. Hitachi neither warrants nor grants licenses of any rights of Hitachi's or any third party's patent, copyright, trademark, or other intellectual property rights for information contained in this document. Hitachi bears no responsibility for problems that may arise with third party's rights, including intellectual property rights, in connection with use of the information contained in this document.
2. Products and product specifications may be subject to change without notice. Confirm that you have received the latest product standards or specifications before final design, purchase or use.
3. Hitachi makes every attempt to ensure that its products are of high quality and reliability. However, contact Hitachi's sales office before using the product in an application that demands especially high quality and reliability or where its failure or malfunction may directly threaten human life or cause risk of bodily injury, such as aerospace, aeronautics, nuclear power, combustion control, transportation, traffic, safety equipment or medical equipment for life support.
4. Design your application so that the product is used within the ranges guaranteed by Hitachi particularly for maximum rating, operating supply voltage range, heat radiation characteristics, installation conditions and other characteristics. Hitachi bears no responsibility for failure or damage when used beyond the guaranteed ranges. Even within the guaranteed ranges, consider normally foreseeable failure rates or failure modes in semiconductor devices and employ systemic measures such as fail-safes, so that the equipment incorporating Hitachi product does not cause bodily injury, fire or other consequential damage due to operation of the Hitachi product.
5. This product is not designed to be radiation resistant.
6. No one is permitted to reproduce or duplicate, in any form, the whole or part of this document without written approval from Hitachi.
7. Contact Hitachi's sales office for any questions regarding this document or Hitachi semiconductor products.

HITACHI

Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	NorthAmerica	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
	Asia (Singapore)	: http://www.has.hitachi.com.sg/grp3/sicd/index.htm
	Asia (Taiwan)	: http://www.hitachi.com.tw/E/Product/SICD_Frame.htm
	Asia (HongKong)	: http://www.hitachi.com.hk/eng/bo/grp3/index.htm
	Japan	: http://www.hitachi.co.jp/Sicd/indx.htm

For further information write to:

Hitachi Semiconductor (America) Inc. 179 East Tasman Drive, San Jose, CA 95134 Tel: <1> (408) 433-1990 Fax: <1> (408) 433-0223	Hitachi Europe GmbH Electronic components Group Dornacher Straße 3 D-85622 Feldkirchen, Munich Germany Tel: <49> (89) 9 9180-0 Fax: <49> (89) 9 29 30 00 Hitachi Europe Ltd. Electronic Components Group. Whitebrook Park Lower Cookham Road Maidenhead Berkshire SL6 8YA, United Kingdom Tel: <44> (1628) 585000 Fax: <44> (1628) 778322
--	---

Hitachi Asia Pte. Ltd. 16 Collyer Quay #20-00 Hitachi Tower Singapore 049318 Tel: 535-2100 Fax: 535-1533 Hitachi Asia Ltd. Taipei Branch Office 3F, Hung Kuo Building, No.167, Tun-Hwa North Road, Taipei (105) Tel: <886> (2) 2718-3666 Fax: <886> (2) 2718-8180
--

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower, World Finance Centre,
Harbour City, Canton Road, Tsim Sha Tsui,
Kowloon, Hong Kong
Tel: <852> (2) 735 9218
Fax: <852> (2) 730 0281
Telex: 40815 HITEC HX

Copyright ' Hitachi, Ltd., 1999. All rights reserved. Printed in Japan.